

U.S. Department of Commerce, Patent and Trademark Office						Atty Docket No.	Serial No.	
						M-11822 US	09/925,102	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT						Applicant(s)		
(Use several sheets if necessary)						Jack H. Yuan et al.		
						Filing Date	Group	
						August 8, 2001	2185	
U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AA	5,043,940	Aug. 27, 1991	Harari			RECEIVED JUL 30 2002 Technology Center 2100	
	AB	5,070,032	Dec. 3, 1991	Yuan et al.				
	AC	5,095,344	Mar. 10, 1992	Harari				
	AD	5,172,338	Dec. 15, 1992	Mehrotra et al.				
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	AF	5,313,421	May 17, 1994	Guterman et al.				
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	AH	5,343,063	Aug. 30, 1994	Yuan et al.				
	AI	5,661,053	Aug. 26, 1997	Yuan				
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	AK	6,103,573	Aug. 15, 2000	Harari et al.				
Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
	AL	Aritome, Seiichi, "Advanced Flash Memory Technology and Trends for File Storage Application," IEDM Technical Digest, International Electronic Devices Meeting, IEEE, San Francisco, California, December 10-13, 2000, pp 33.1.1-33.1.4.						
	AM	Takeuchi, Y., et al., "A Self-Aligned STI Process Integration for Low Cost and Highly Reliable 1Gbit Flash Memories," 1998 Symposium on VLSI Technology; Digest of Technical Papers, IEEE, Honolulu, Hawaii, June 9-11, 1998, pp. 102-103.						
	AN	Lee, Jae-Duk, et al., "Effects of Parasitic Capacitance on NAND Flash Memory Cell Operation," Non-Volatile Semiconductor Memory Workshop, IEEE, Monterey, California, August 12-16, 2001, pp. 90-92.						
	AO-	Chan, et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," <i>IEEE Electron Device Letters</i> , Vol. EDL-8, No. 3, March 1987, pp. 93-95.						
Examiner			Date Considered					
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.								

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U.S. Patent Documents								
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate	
	AP	6,151,248	Nov. 21, 2000	Harari et al.				
	AQ	6,222,762	Apr. 24, 2001	Guterman et al.				
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		Document	Date	Country	Class	Subclass	Yes	No
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	AR	Nozaki et al., "A 1-Mb EEPROM with MONOS Memory Cell for Semiconductor Disk Application," <i>IEEE Journal of Solid State Circuits</i> , Vol. 26, No. 4, April 1991, pp. 497-501.						
	AS	Eitan et al., "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell," <i>IEEE Electron Device Letters</i> , Vol. 21, No. 11, November 2000, pp. 543-545.						
	AT	DiMaria et al., "Electrically-alterable read-only-memory using Si-rich SiO ₂ injectors and a floating polycrystalline silicon storage layer," <i>J. Appl. Phys.</i> 52(7), July 1981, pp. 4825-4842.						
	AU	Hori et al., "A MOSFET with Si-implanted Gate-SiO ₂ Insulator for Nonvolatile Memory Applications," <i>IEDM</i> 92, April 1992, pp. 469-472.						
Examiner			Date Considered					
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